Maximum Ratings (@T_A = +25°C unless otherwise specified)

Characteristic			Symbol	Value	Units
Drain-Source Voltage			V_{DSS}	60	V
Gate-Source Voltage			V_{GSS}	±20	V
Continuous Drain Current (Note 7) V_{GS} = 10V	Steady State	T_A = +25°C T_A = +70°C	I_D	5.0 4.1	A
	t<10s	T_A = +25°C T_A = +70°C	I_D	6.6 5.3	A
Maximum Body Diode Forward Current (Note 7)			I_S	2.5	A
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)			I_{DM}	30	A
Pulsed Body Diode Forward Current (10µs pulse, duty cycle = 1%)			I_{SM}	30	A
Avalanche Current (Note 8) L = 0.1mH			I_{AS}	14.2	A
Avalanche Energy (Note 8) L = 0.1mH			E_{AS}	10	mJ

Thermal Characteristics (@T_A = +25°C unless otherwise specified)

Characteristic		Symbol	Value	Units
Total Power Dissipation (Note 6)	T_A = +25°C	P_D	1.3	W
	T_A = +70°C		0.8	
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	$R_{\theta JA}$	102	°C/W
	t<10s		61	
Total Power Dissipation (Note 7)	T_A = +25°C	P_D	1.7	W
	T_A = +70°C		1.1	
Thermal Resistance, Junction to Ambient (Note 7)	Steady State	$R_{\theta JA}$	75	°C/W
	t<10s		50	
Thermal Resistance, Junction to Case (Note 7)		$R_{\theta JC}$	14.5	
Operating and Storage Temperature Range		T_J, T_{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = 25°C unless otherwise specified)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 9)						
Drain-Source Breakdown Voltage	BV_{DSS}	60	—	—	V	V_{GS} = 0V, I_D = 250µA
Zero Gate Voltage Drain Current	I_{DSS}	—	—	100	nA	V_{DS} = 60V, V_{GS} = 0V
Gate-Source Leakage	I_{GSS}	—	—	±100	nA	V_{GS} = ±20V, V_{DS} = 0V
ON CHARACTERISTICS (Note 9)						
Gate Threshold Voltage	$V_{GS(TH)}$	1	—	3	V	V_{DS} = V_{GS}, I_D = 250µA
Static Drain-Source On-Resistance	$R_{DS(ON)}$	—	30	40	mΩ	V_{GS} = 10V, I_D = 4.5A
		—	35	55		V_{GS} = 4.5V, I_D = 3.5A
Forward Transfer Admittance	$\|Y_{FS}\|$	—	4.5	—	S	V_{DS} = 10V, I_D = 4.3A
Diode Forward Voltage	V_{SD}	—	0.7	1.2	V	V_{GS} = 0V, I_S = 1A
DYNAMIC CHARACTERISTICS (Note 10)						
Input Capacitance	C_{ISS}	—	1,287	—	pF	V_{DS} = 25V, V_{GS} = 0V f = 1.0MHz
Output Capacitance	C_{OSS}	—	57	—		
Reverse Transfer Capacitance	C_{RSS}	—	44	—		
Gate Resistance	R_G	—	1.2	—	Ω	V_{DS} = 0V, V_{GS} = 0V, f = 1.0MHz
Total Gate Charge (V_{GS} = 10V)	Q_G	—	22.4	—	nC	V_{DS} = 30V, I_D = 4.3A
Total Gate Charge (V_{GS} = 4.5V)	Q_G	—	10.4	—		
Gate-Source Charge	Q_{GS}	—	4.9	—		
Gate-Drain Charge	Q_{GD}	—	3.0	—		
Turn-On Delay Time	$t_{D(ON)}$	—	6.6	—	ns	V_{GS} = 10V, V_{DD} = 30V, R_G = 6Ω, I_D = 4.3A
Turn-On Rise Time	t_R	—	8.1	—		
Turn-Off Delay Time	$t_{D(OFF)}$	—	20.1	—		
Turn-Off Fall Time	t_F	—	4.0	—		
Body Diode Reverse Recovery Time	t_{RR}	—	18	—	ns	I_S = 4.3A, di/dt = 100A/µs
Body Diode Reverse Recovery Charge	Q_{RR}	—	11.9	—	nC	I_S = 4.3A, di/dt = 100A/µs

Notes: 6. Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided.
7. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1-inch square copper plate.
8. I_{AS} and E_{AS} rating are based on low frequency and duty cycles to keep T_J = +25°C.
9. Short duration pulse test used to minimize self-heating effect.
10. Guaranteed by design. Not subject to product testing.

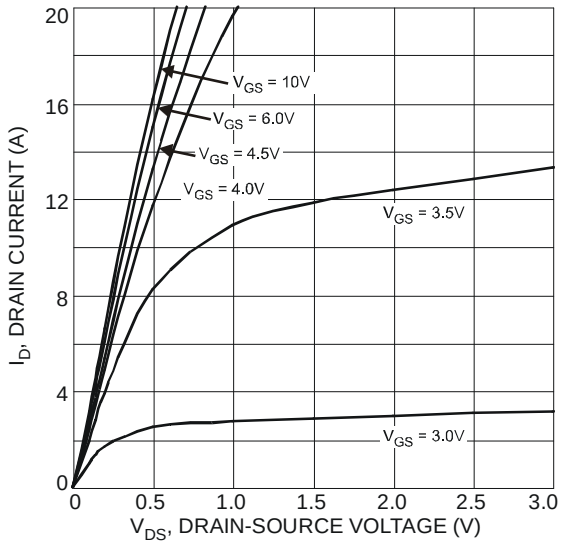


Fig.1 Typical Output Characteristic

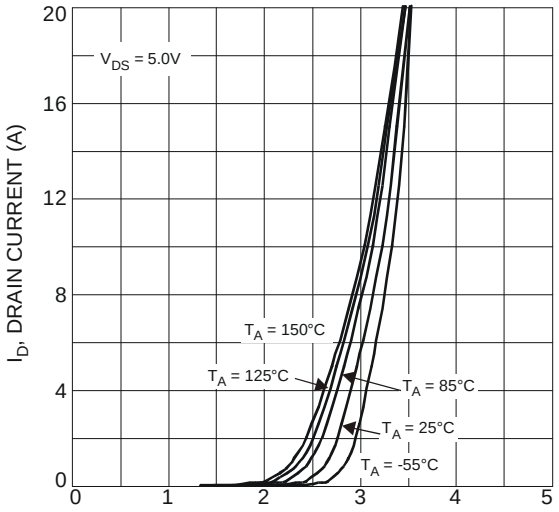


Fig.2 Typical Transfer Characteristics

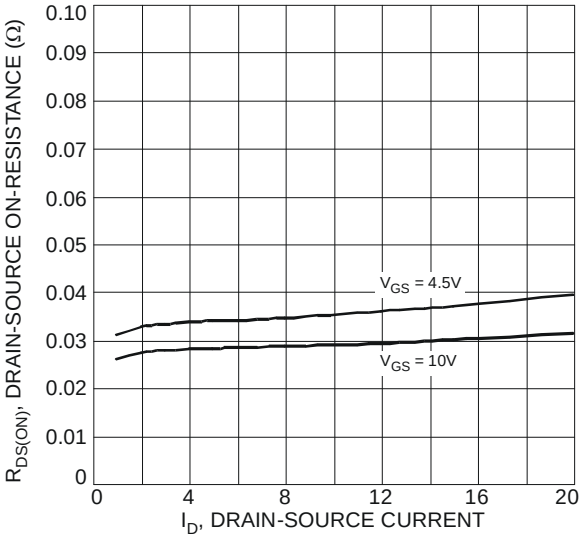


Fig. 3 Typical On-Resistance vs. Drain Current and Gate Voltage

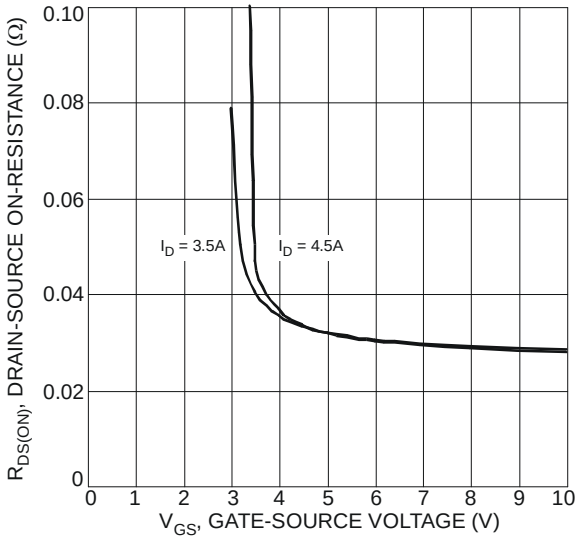


Fig. 4 Typical On-Resistance vs. Drain Current and Gate Voltage

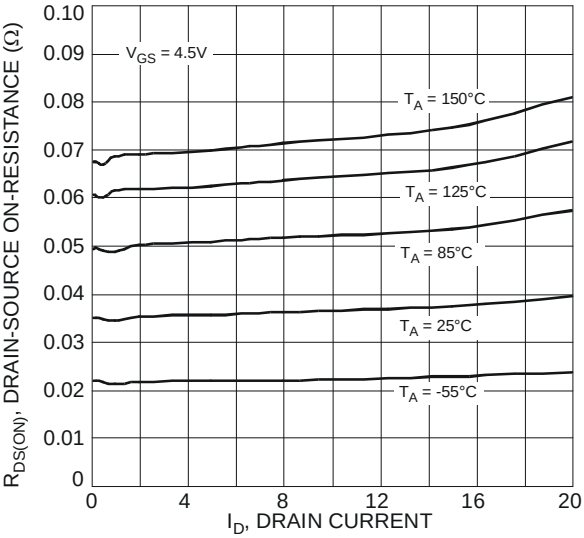


Fig. 5 Typical On-Resistance vs. Drain Current and Temperature

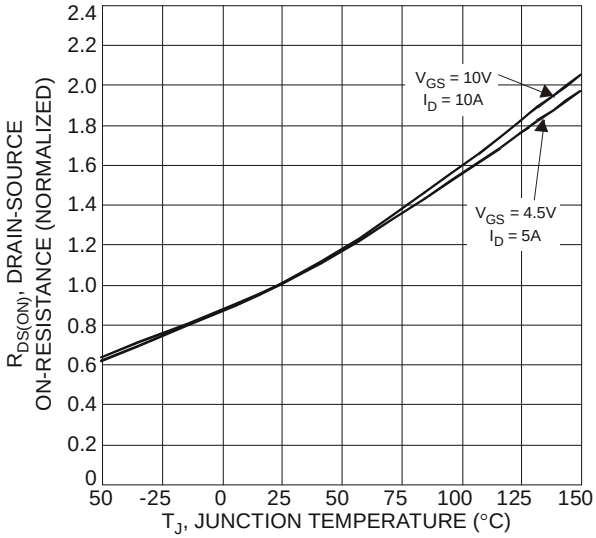


Fig. 6 On-Resistance Variation with Temperature

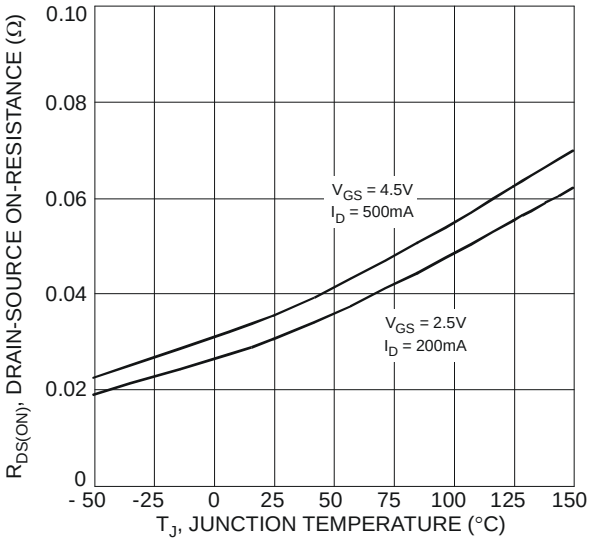


Fig. 7 On-Resistance Variation with Temperature

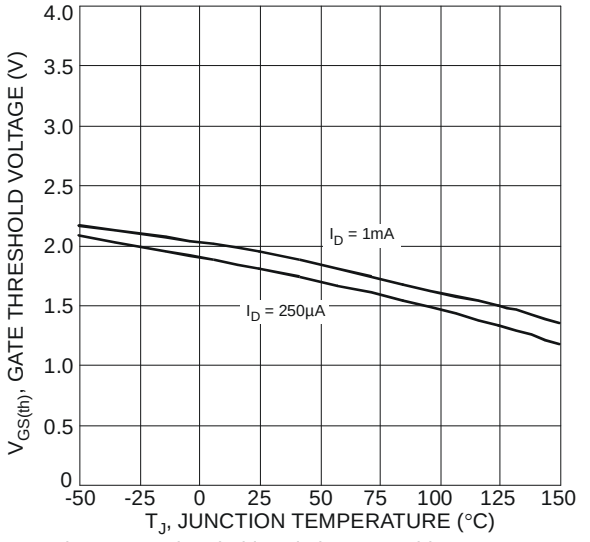


Fig. 8 Gate Threshold Variation vs. Ambient Temperature

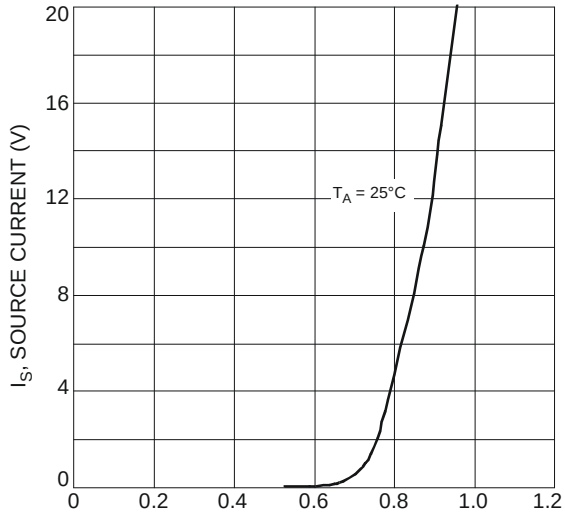


Fig.9 Diode Forward Voltage vs. Current

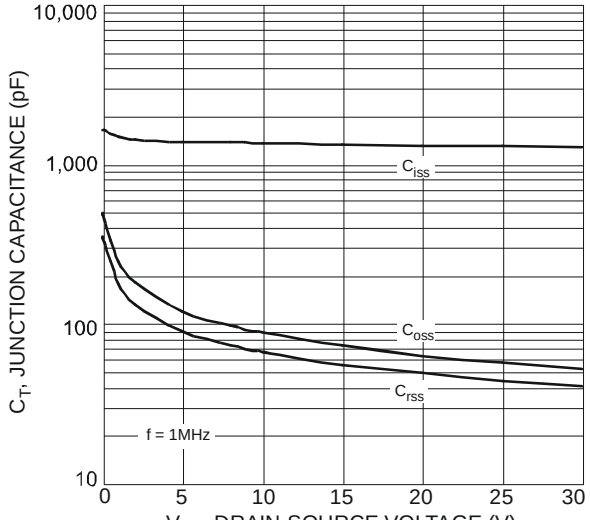


Fig. 10 Typical Junction Capacitance

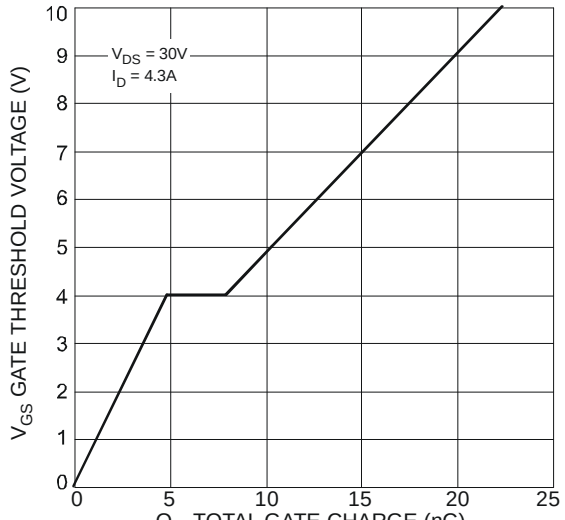


Fig. 11 Gate Charge

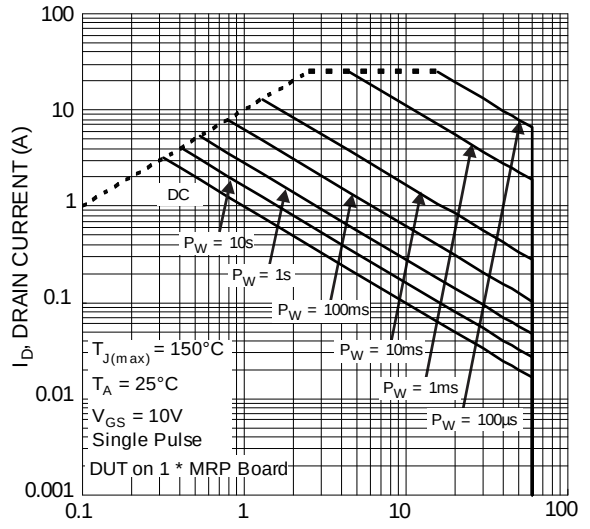


Figure 12 SOA, Safe Operation Area

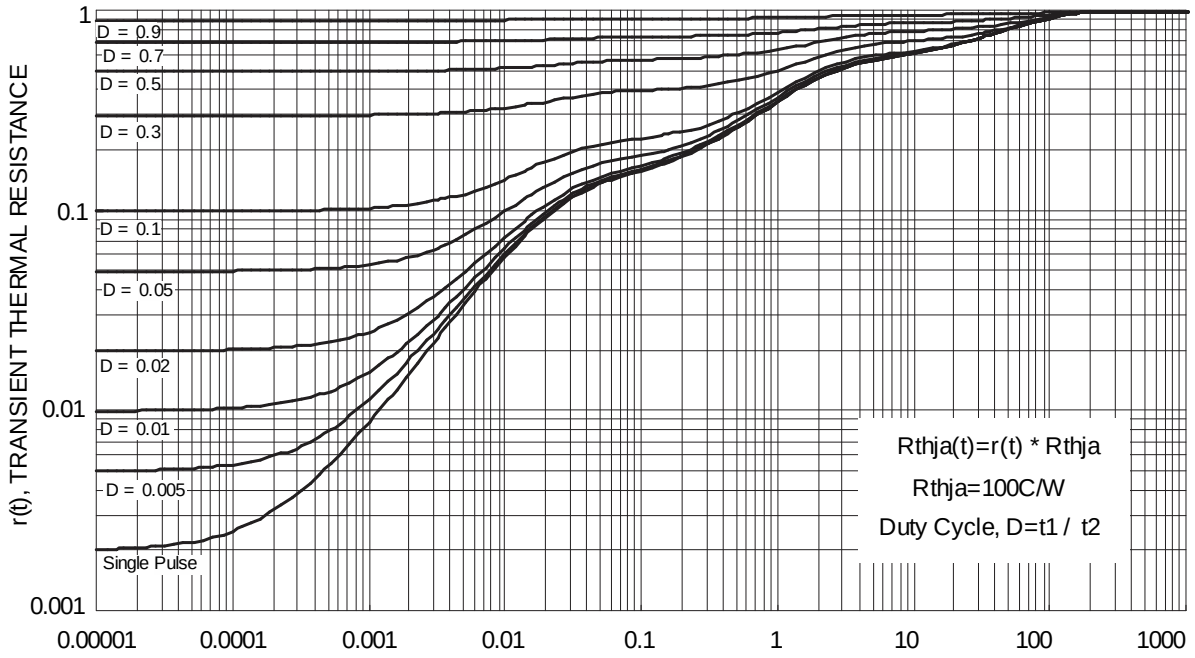
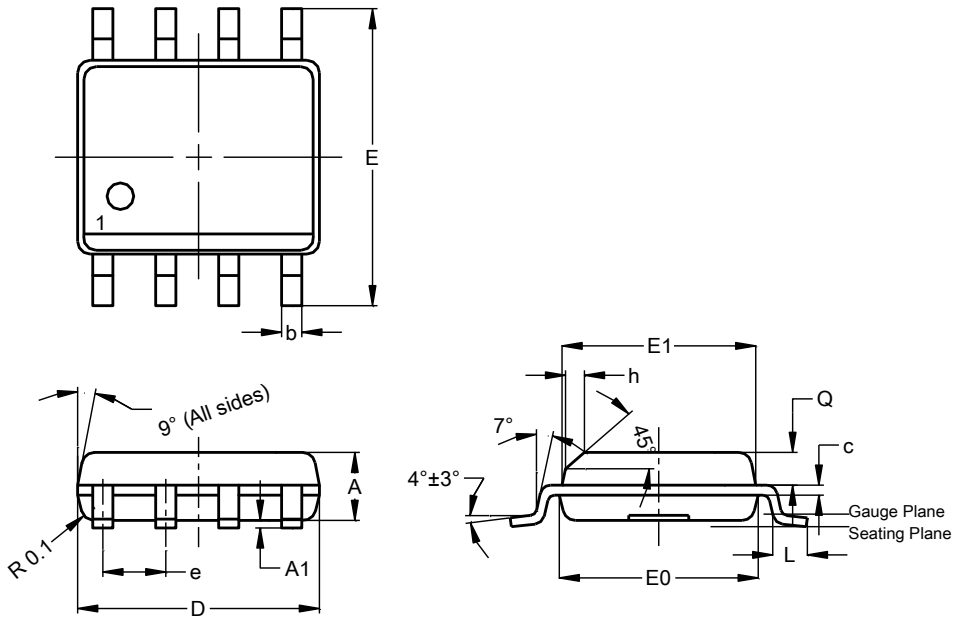


Figure 13 Transient Thermal Resistance

Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

SO-8

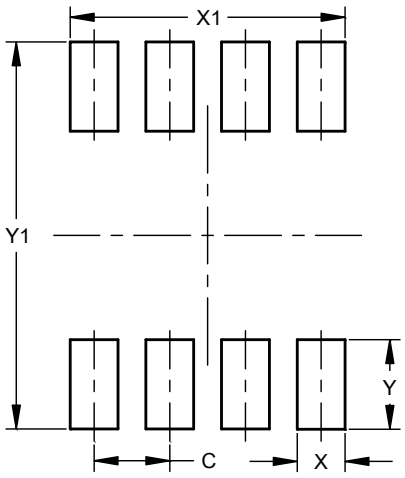


SO-8			
Dim	**Min**	**Max**	**Typ**
A	1.40	1.50	1.45
A1	0.10	0.20	0.15
b	0.30	0.50	0.40
c	0.15	0.25	0.20
D	4.85	4.95	4.90
E	5.90	6.10	6.00
E1	3.80	3.90	3.85
E0	3.85	3.95	3.90
e	--	--	1.27
h	-	--	0.35
L	0.62	0.82	0.72
Q	0.60	0.70	0.65
All Dimensions in mm			

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

SO-8



Dimensions	Value (in mm)
C	1.27
X	0.802
X1	4.612
Y	1.505
Y1	6.50

IMPORTANT NOTICE

DIODES INCORPORATED MAKES NO WARRANTY OF ANY KIND, EXPRESS OR IMPLIED, WITH REGARDS TO THIS DOCUMENT, INCLUDING, BUT NOT LIMITED TO, THE IMPLIED WARRANTIES OF MERCHANTABILITY AND FITNESS FOR A PARTICULAR PURPOSE (AND THEIR EQUIVALENTS UNDER THE LAWS OF ANY JURISDICTION).

Diodes Incorporated and its subsidiaries reserve the right to make modifications, enhancements, improvements, corrections or other changes without further notice to this document and any product described herein. Diodes Incorporated does not assume any liability arising out of the application or use of this document or any product described herein; neither does Diodes Incorporated convey any license under its patent or trademark rights, nor the rights of others. Any Customer or user of this document or products described herein in such applications shall assume all risks of such use and will agree to hold Diodes Incorporated and all the companies whose products are represented on Diodes Incorporated website, harmless against all damages.

Diodes Incorporated does not warrant or accept any liability whatsoever in respect of any products purchased through unauthorized sales channel. Should Customers purchase or use Diodes Incorporated products for any unintended or unauthorized application, Customers shall indemnify and hold Diodes Incorporated and its representatives harmless against all claims, damages, expenses, and attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized application.

Products described herein may be covered by one or more United States, international or foreign patents pending. Product names and markings noted herein may also be covered by one or more United States, international or foreign trademarks.

This document is written in English but may be translated into multiple languages for reference. Only the English version of this document is the final and determinative format released by Diodes Incorporated.

LIFE SUPPORT

Diodes Incorporated products are specifically not authorized for use as critical components in life support devices or systems without the express written approval of the Chief Executive Officer of Diodes Incorporated. As used herein:

A. Life support devices or systems are devices or systems which:

1. are intended to implant into the body, or
2. support or sustain life and whose failure to perform when properly used in accordance with instructions for use provided in the labeling can be reasonably expected to result in significant injury to the user.

B. A critical component is any component in a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or to affect its safety or effectiveness.

Customers represent that they have all necessary expertise in the safety and regulatory ramifications of their life support devices or systems, and acknowledge and agree that they are solely responsible for all legal, regulatory and safety-related requirements concerning their products and any use of Diodes Incorporated products in such safety-critical, life support devices or systems, notwithstanding any devices- or systems-related information or support that may be provided by Diodes Incorporated. Further, Customers must fully indemnify Diodes Incorporated and its representatives against any damages arising out of the use of Diodes Incorporated products in such safety-critical, life support devices or systems.

www.diodes.com